

ABSTRACT

A photolithography mask for optically transferring a pattern formed in the mask onto a substrate and for negating optical proximity effects. The mask includes a plurality of resolvable features to be printed on the substrate, and at least one non-resolvable optical proximity correction feature disposed between two of the resolvable features to be printed, where the non-resolvable optical proximity correction feature has a transmission coefficient in the range of greater than 0% to less than 100%.